

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently amended) A method of forming a fin for a fin field effect transistor (FinFET), comprising:

defining a trench in a layer of first material;

growing a second material in the trench to form the fin; and

forming a spacer on an upper surface of the fin;

removing the layer of first material;

forming a liner on the spacer and fin, the liner comprising a third material.

2. (original) The method of claim 1, wherein the first material comprises an oxide.

3. (original) The method of claim 1, wherein defining a trench comprises:

forming the layer of first material on a substrate; and

selectively etching the layer to define the trench.

4. (original) The method of claim 1, wherein growing the second material comprises epitaxially growing the second material.

5. (original) The method of claim 1, wherein removing the layer of first material comprises stripping the layer.

6. (Canceled)

7. (Currently amended) The method of claim ~~[[6]]~~ 1, wherein forming the spacer comprises depositing a third material on the upper surface.

8. (original) The method of claim 7, wherein the third material comprises a nitride.

9. (original) The method of claim 1, wherein the second material comprises silicon.

10. (Canceled)

11. (Currently amended) The method of claim ~~[[10]]~~ 1, wherein the third material comprises a nitride.

12. (Currently amended) The method of claim ~~[[10]]~~ 1, wherein the third material comprises an oxide.

13. (Currently amended) The method of claim ~~[[10]]~~ 1, further comprising:  
removing the spacer and liner.

14. (original) The method of claim 13, wherein removing the spacer and liner comprises:  
stripping the spacer and liner.

15-19. (Canceled)

20. (New) A method of forming a fin for a fin field effect transistor (FinFET), comprising:  
defining a trench in a layer of first material;  
growing a second material in the trench to form the fin;  
removing the layer of first material;  
forming a liner on the fin, the liner comprising a third material; and  
removing the liner to leave the fin.

21. (New) The method of claim 20, wherein growing the second material comprises:  
epitaxially growing the second material.

22. (New) The method of claim 20, wherein removing the liner comprises:  
stripping the liner.

23. (New) A method of forming a fin for a fin field effect transistor (FinFET), comprising:  
defining a trench in a layer of first material, wherein a width of an opening of the trench  
is substantially smaller than a thickness of the layer;

growing a second material in the trench to form the fin; and  
removing the layer of first material.

24. (New) The method of claim 23, further comprising:  
forming a liner on the fin, the liner comprising a third material; and  
removing the liner to leave the fin.